#### IMPERFECTIONS IN SOLIDS

#### Single crystals

- Periodic and repeated arrangement of atoms is perfect or extends throughout the entirety of the specimen
- Translation: integer multiple of lattice constants → identical position in another unit cell
- Can be produced naturally and artificially( eg. Si: Czochralski)



### Types of Imperfections

- Vacancy atoms
- Interstitial atoms
- Substitutional atoms
- Dislocations
- Grain Boundaries

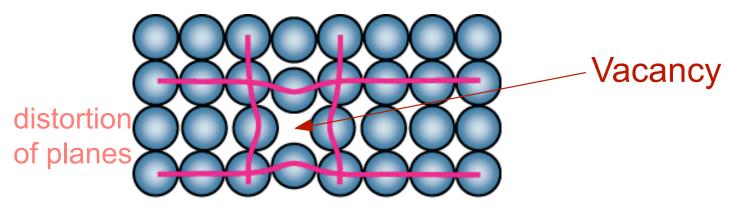
Point defects

Line defects

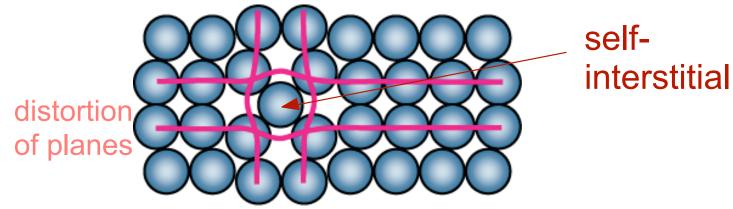
Area defects

#### **Point Defects**

- Vacancies:
  - -vacant atomic sites in a structure.

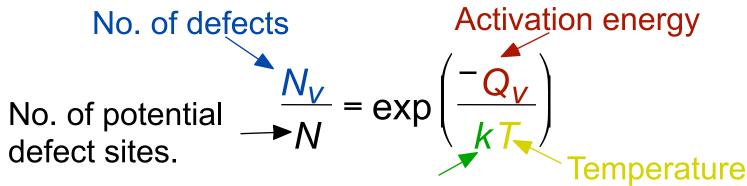


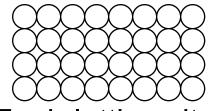
- Self-Interstitials:
  - -"extra" atoms positioned between atomic sites.



# Equilibrium Concentration: Point Defects

Equilibrium concentration varies with temperature!





Each lattice site is a potential vacancy site

#### Boltzmann's constant

 $(1.38 \times 10^{-23} \text{ J/atom-K})$ 

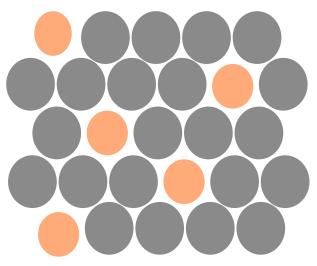
 $(8.62 \times 10^{-5} \text{ eV/atom-K})$ 

#### Point Defects in Alloys

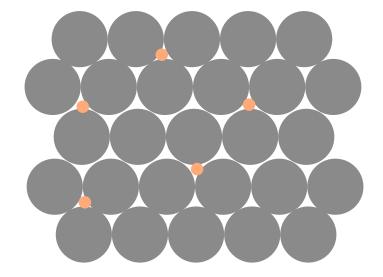
OR

Two outcomes if impurity (B) added to host (A):

Solid solution of B in A (i.e., random dist. of point defects)



Substitutional solid soln. (e.g., Cu in Ni)



Interstitial solid soln. (e.g., C in Fe)

Conditions for substitutional solid solution (S.S.)

- W. Hume Rothery rule
  - − 1.  $\Delta r$  (atomic radius) < 15%
  - 2. Proximity in periodic table
    - i.e., similar electronegativities
  - 3. Same crystal structure for pure metals
  - 4. Valency
    - All else being equal, a metal will have a greater tendency to dissolve a metal of higher valency than one of lower valency

Specification of composition

$$C_1 = \frac{m_1}{m_1 + m_2} \times 100$$

 $m_1$  = mass of component 1

$$C_1' = \frac{n_{m1}}{n_{m1} + n_{m2}} \times 100$$

 $n_{m1}$  = number of moles of component 1

#### **Linear Defects**

#### Linear Defects (Dislocations)

Are one-dimensional defects around which atoms are misaligned

Burgers vector, **b**: measure of lattice distortion

#### **Edge Dislocation**

- extra half-plane of atoms inserted in a crystal structure
- **b**  $\perp$  to dislocation line

Edge dislocation line

#### **Burgers vector**

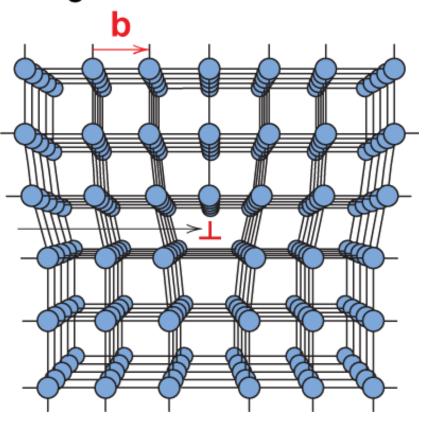
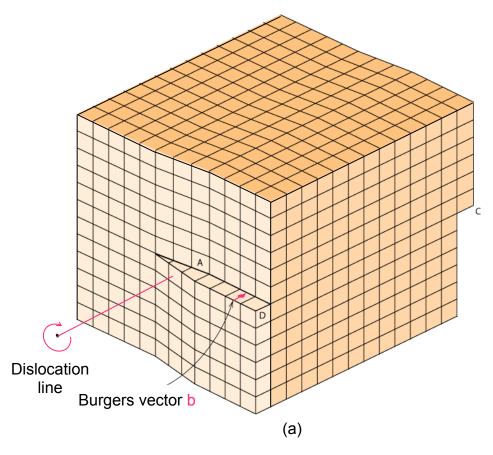


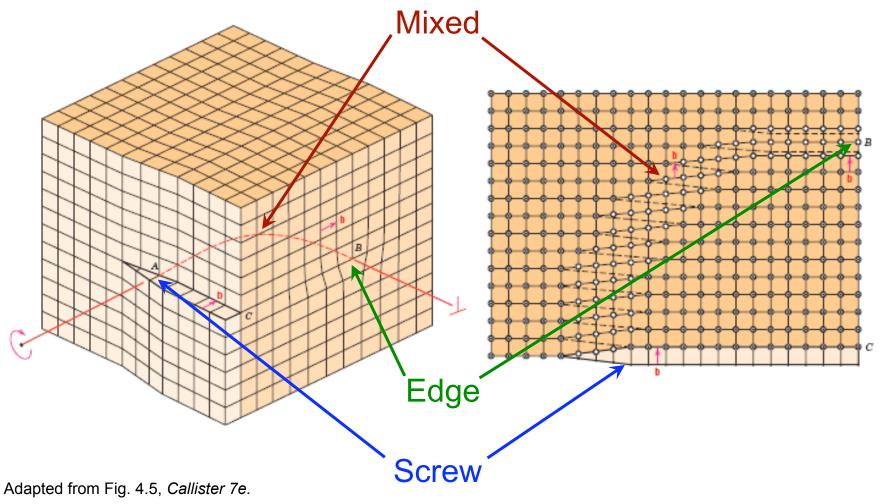
Fig. 4.3, Callister 7e.

#### **Screw Dislocation**

spiral planar ramp resulting from shear deformation  $\mathbf{b} \parallel$  to dislocation line



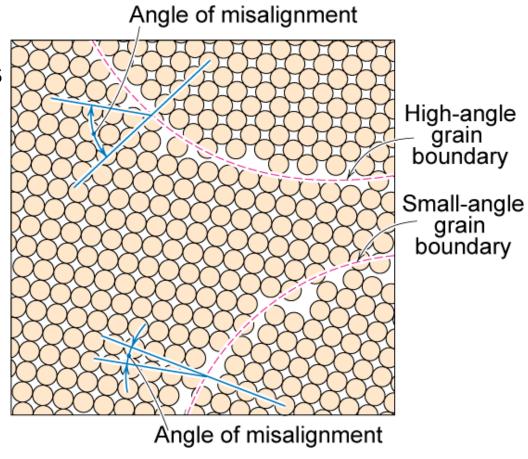
#### Edge, Screw, and Mixed Dislocations



#### **Grain Boundaries and Polycrystalline Materials**

#### **Grain Boundaries**

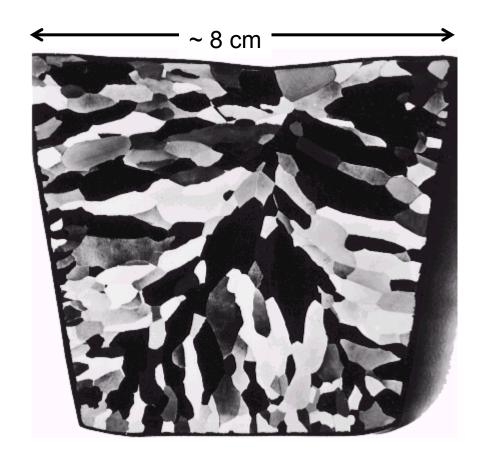
- regions between crystals
- transition from lattice of one region to that of the other
- slightly disordered
- low density in grain boundaries
  - high mobility
  - high diffusivity
  - high chemical reactivity



Adapted from Fig. 4.7, Callister 7e.



### Polycrystalline Materials



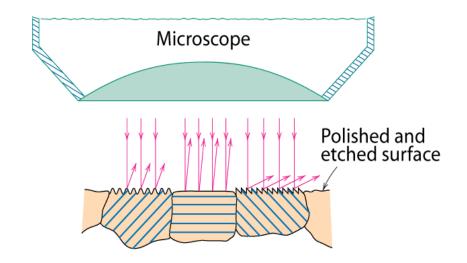
Optical Micrograph of Polycrystalline lead ingot

# Microscopic Examination

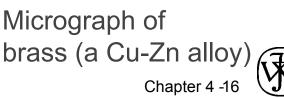
- Crystallites (grains) and grain boundaries.
  Vary considerably in size. Can be quite large
  - ex: Large single crystal of quartz or diamond or Si
  - ex: Aluminum light post or garbage can see the individual grains
- Crystallites (grains) can be quite small (mm or less) – necessary to observe with a microscope.

# **Optical Microscopy**

- Can resolve features as small as ~λ/2 (eg. ~250 nm).
- Polishing removes surface features (e.g., scratches)
- Etching changes reflectance, depending on crystal orientation.







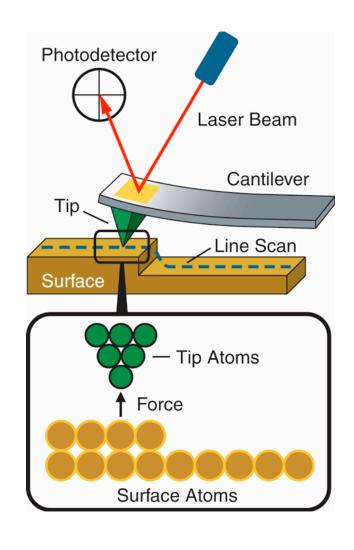
# Microscopy

Optical resolution ca. ~10<sup>-7</sup> m ~ 250 nm For higher resolution need shorter wavelength

- X-Rays? Difficult to focus (Synchrotron).
- Electrons (SEM, TEM)
  - wavelengths ca. 3 pm (0.003 nm)
    - (Magnification 1,000,000X)
  - Atomic resolution possible
  - Electron beam focused by magnetic lenses.

# **Atomic Force Microscope**

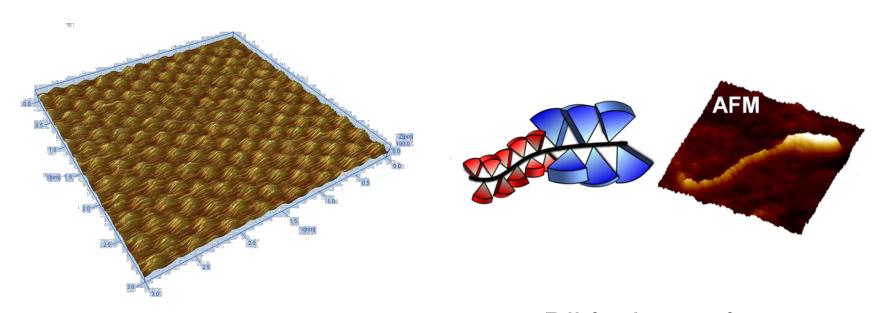
(a type of Scanning Probe Microscope)





### **Atomic Force Microscope**

(a type of Scanning Probe Microscope)



Graphite atoms

Diblock copolymer

#### Relevant Courses in MSE

MSE 331 Crystallography and Structure (3) Fall

MSE 333 Materials Characterization (3) Spring-Rolandi

MSE 484 Materials Chemistry (3)- NW Raschke

MSE 510 Bonding, Crystallography, and Symmetry-Related Properties of Materials (3)

MSE 512 Experimental Transmission Electron Microscopy (3)

MSE 541 Defects in Materials (3)